EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	10	cmos and test adj structure and electrical adj short	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:11
S2	2136	(438/14).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/18 10:53
S3	165	(438/6).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/18 10:58
S4	691	(438/10).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/18 11:09
S5	3956	(438/17).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/18 14:19
S6	602	(438/18).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/18 14:43
S7	348	(324/718).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/18 14:47
S8	490	(324/719).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/18 14:59

EAST Search History

S9	1	reticle and cell and test adj voltage and second adj polysilicon adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:01
S10	4	(("4800418") or ("5523252")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/18 15:01
S11	17	("4800418").URPN.	USPAT	OR	ON	2006/05/18 15:02
S12	11	("5523252").URPN.	USPAT	OR	ON	2006/05/18 15:06
S13	121	yem or yield adj evaluation adj module	USPAT	OR	ON	2006/05/18 15:06
S14	0	product adj characterization adj module	USPAT	OR	ON	2006/05/18 15:07
S15	15776	pcm	USPAT	OR	ON	2006/05/18 15:07
S16	0	S13 and S15	USPAT	OR	ON	2006/05/18 15:07
S17	11319	reticle	USPAT	OR	ON	2006/05/18 15:07
S18	2	S13 and S17	USPAT	OR	ON	2006/05/18 15:07
S19	5	257/e21.524	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:12
S20	0	(semiconductor and test adj voltage and cell adj type and second adj polysilicon and (measure adj current or measuring adj current) and interconnect).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/18 15:27